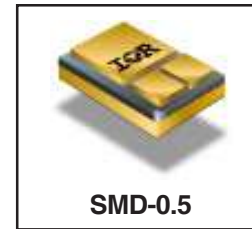


**RADIATION HARDENED  
POWER MOSFET  
SURFACE MOUNT (SMD-0.5)**

**IRHNJ9230  
200V, P-CHANNEL  
RAD Hard™ HEXFET® TECHNOLOGY**

**Product Summary**

| Part Number | Radiation Level | RDS(on) | ID    |
|-------------|-----------------|---------|-------|
| IRHNJ9230   | 100K Rads (Si)  | 0.8Ω    | -6.5A |
| IRHNJ93230  | 300K Rads (Si)  | 0.8Ω    | -6.5A |



International Rectifier's RADHard HEXFET® technology provides high performance power MOSFETs for space applications. This technology has over a decade of proven performance and reliability in satellite applications. These devices have been characterized for both Total Dose and Single Event Effects (SEE). The combination of low Rds(on) and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

**Features:**

- Single Event Effect (SEE) Hardened
- Ultra Low RDS(on)
- Low Total Gate Charge
- Proton Tolerant
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Surface Mount
- Ceramic Package
- Light Weight
- ESD Rating: Class 1B per MIL-STD-750, Method 1020

**Absolute Maximum Ratings**

**Pre-Irradiation**

|                             | Parameter                       |               | Units |
|-----------------------------|---------------------------------|---------------|-------|
| ID @ VGS = -12V, TC = 25°C  | Continuous Drain Current        | -6.5          | A     |
| ID @ VGS = -12V, TC = 100°C | Continuous Drain Current        | -4.1          |       |
| IDM                         | Pulsed Drain Current ①          | -26           |       |
| PD @ TC = 25°C              | Max. Power Dissipation          | 75            | W     |
|                             | Linear Derating Factor          | 0.6           | W/°C  |
| VGS                         | Gate-to-Source Voltage          | ± 20          | V     |
| EAS                         | Single Pulse Avalanche Energy ② | 165           | mJ    |
| IAR                         | Avalanche Current ①             | -6.5          | A     |
| EAR                         | Repetitive Avalanche Energy ①   | 7.5           | mJ    |
| dv/dt                       | Peak Diode Recovery dv/dt ③     | -27           | V/ns  |
| TJ                          | Operating Junction              | -55 to 150    | °C    |
| TSTG                        | Storage Temperature Range       |               |       |
|                             | Package Mounting Surface Temp.  | 300 (for 5s)  |       |
|                             | Weight                          | 1.0 (Typical) | g     |

For footnotes, refer to the last page

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**Electrical Characteristics @ T<sub>j</sub> = 25°C (Unless Otherwise Specified)**

|                                     | Parameter                                    | Min  | Typ   | Max  | Units | Test Conditions   |
|-------------------------------------|--|------|-------|------|-------|---|
| BV <sub>DSS</sub>                   | Drain-to-Source Breakdown Voltage            | -200 | —     | —    | V     | V <sub>GS</sub> = 0 V, I <sub>D</sub> = -1.0mA  |
| ΔBV <sub>DSS</sub> /ΔT <sub>J</sub> | Temperature Coefficient of Breakdown Voltage | —    | -0.27 | —    | V/°C  | Reference to 25°C, I <sub>D</sub> = -1.0mA  |
| R <sub>DS(on)</sub>                 | Static Drain-to-Source On-State Resistance   | —    | —     | 0.8  | Ω     | V <sub>GS</sub> = -12V, I <sub>D</sub> = -4.1A ④  |
| V <sub>GS(th)</sub>                 | Gate Threshold Voltage                       | -2.0 | —     | -4.0 | V     | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -1.0mA                                       |
| g <sub>fs</sub>                     | Forward Transconductance                     | 2.0  | —     | —    | S     | V <sub>DS</sub> = -15V, I <sub>DS</sub> = -4.1A ④   |
| I <sub>DSS</sub>                    | Zero Gate Voltage Drain Current              | —    | —     | -25  | μA    | V <sub>DS</sub> = -160V, V <sub>GS</sub> = 0V   |
|                                     |  | —    | —     | -250 |       | V <sub>DS</sub> = -160V<br>V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C                           |
| I <sub>GSS</sub>                    | Gate-to-Source Leakage Forward               | —    | —     | -100 | nA    | V <sub>GS</sub> = -20V  |
| I <sub>GSS</sub>                    | Gate-to-Source Leakage Reverse               | —    | —     | 100  |       | V <sub>GS</sub> = 20V   |
| Q <sub>g</sub>                      | Total Gate Charge                            | —    | —     | 45   | nC    | V <sub>GS</sub> = -12V, I <sub>D</sub> = -6.5A<br>V <sub>DS</sub> = -100V                         |
| Q <sub>gs</sub>                     | Gate-to-Source Charge                        | —    | —     | 10   |       |   |
| Q <sub>gd</sub>                     | Gate-to-Drain ('Miller') Charge              | —    | —     | 25   |       |   |
| t <sub>d(on)</sub>                  | Turn-On Delay Time                           | —    | —     | 30   | ns    | V <sub>DD</sub> = -100V, I <sub>D</sub> = -6.5A,<br>V <sub>GS</sub> = -12V, R <sub>G</sub> = 7.5Ω |
| t <sub>r</sub>                      | Rise Time                                    | —    | —     | 50   |       |   |
| t <sub>d(off)</sub>                 | Turn-Off Delay Time                          | —    | —     | 75   |       |   |
| t <sub>f</sub>                      | Fall Time                                    | —    | —     | 65   |       |   |
| L <sub>S</sub> + L <sub>D</sub>     | Total Inductance                             | —    | 4.0   | —    | nH    | Measured from the center of drain pad to center of source pad                                     |
| C <sub>iss</sub>                    | Input Capacitance                            | —    | 1360  | —    | pF    | V <sub>GS</sub> = 0V, V <sub>DS</sub> = -25V<br>f = 1.0MHz  |
| C <sub>oss</sub>                    | Output Capacitance                           | —    | 190   | —    |       |   |
| C <sub>rss</sub>                    | Reverse Transfer Capacitance                 | —    | 40    | —    |       |   |

**Source-Drain Diode Ratings and Characteristics**

|                 | Parameter                              | Min  | Typ | Max  | Units | Test Conditions   |
|-----------------|--|--|-----|------|-------|---|
| I <sub>S</sub>  | Continuous Source Current (Body Diode) | —  | —   | -6.5 | A     | T <sub>j</sub> = 25°C, I <sub>S</sub> = -6.5A, V <sub>GS</sub> = 0V ④ |
| I <sub>SM</sub> | Pulse Source Current (Body Diode) ①    | —  | —   | -26  |       |   |
| V <sub>SD</sub> | Diode Forward Voltage                  | —  | —   | -5.0 | V     | T <sub>j</sub> = 25°C, I <sub>F</sub> = -6.5A, di/dt ≤ -100A/μs       |
| t <sub>rr</sub> | Reverse Recovery Time                  | —  | —   | 400  | ns    | V <sub>DD</sub> ≤ -25V ④  |
| Q <sub>RR</sub> | Reverse Recovery Charge                | —  | —   | 3.4  | μC    |   |
| t <sub>on</sub> | Forward Turn-On Time                   | Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L <sub>S</sub> + L <sub>D</sub> . |     |      |       |   |

**Thermal Resistance**

|                     | Parameter            | Min | Typ | Max  | Units | Test Conditions                      |
|---------------------|----------------------|-----|-----|------|-------|--------------------------------------|
| R <sub>thJC</sub>   | Junction-to-Case     | —   | —   | 1.67 | °C/W  | Soldered to 1" Sq. Copper clad Board |
| R <sub>thJPCB</sub> | Junction-to-PC Board | —   | 12  | —    |       |                                      |

Note: Corresponding Spice and Saber models are available on International Rectifier Website.

For footnotes, refer to the last page

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

**Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥**

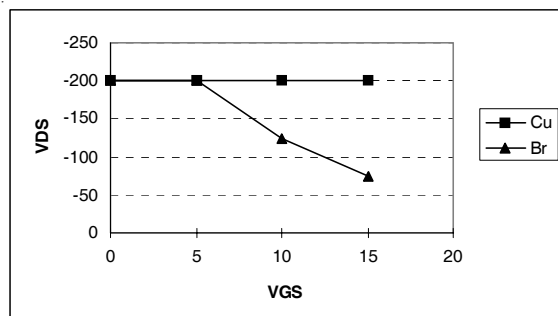
|                     | Parameter  | 100K Rads(Si) <sup>1</sup> |       | 300K Rads (Si) <sup>2</sup> |       | Units | Test Conditions   |
|---------------------|--|----------------------------|-------|-----------------------------|-------|-------|---|
|                     |  | Min                        | Max   | Min                         | Max   |       |   |
| BV <sub>DSS</sub>   | Drain-to-Source Breakdown Voltage                                    | -200                       | —     | -200                        | —     | V     | V <sub>GS</sub> = 0V, I <sub>D</sub> = -1.0mA               |
| V <sub>GS(th)</sub> | Gate Threshold Voltage   | - 2.0                      | -4.0  | -2.0                        | -5.0  |       | V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = -1.0mA |
| I <sub>GSS</sub>    | Gate-to-Source Leakage Forward                                       | —                          | -100  | —                           | -100  | nA    | V <sub>GS</sub> = -20V                                      |
| I <sub>GSS</sub>    | Gate-to-Source Leakage Reverse                                       | —                          | 100   | —                           | 100   |       | V <sub>GS</sub> = 20V                                       |
| I <sub>DSS</sub>    | Zero Gate Voltage Drain Current                                      | —                          | -25   | —                           | -25   | μA    | V <sub>DS</sub> = -160V, V <sub>GS</sub> = 0V               |
| R <sub>DS(on)</sub> | Static Drain-to-Source <sup>④</sup><br>On-State Resistance (TO-3)    | —                          | 0.804 | —                           | 0.804 | Ω     | V <sub>GS</sub> = -12V, I <sub>D</sub> = -4.1A              |
| R <sub>DS(on)</sub> | Static Drain-to-Source <sup>④</sup><br>On-State Resistance (SMD-0.5) | —                          | 0.8   | —                           | 0.8   | Ω     | V <sub>GS</sub> = -12V, I <sub>D</sub> = -4.1A              |
| V <sub>SD</sub>     | Diode Forward Voltage <sup>④</sup>                                   | —                          | -5.0  | —                           | -5.0  | V     | V <sub>GS</sub> = 0V, I <sub>S</sub> = -6.5A                |

1. Part number IRHNJ9230
2. Part number IRHNJ93230

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

**Table 2. Typical Single Event Effect Safe Operating Area**

| Ion | LET<br>MeV/(mg/cm <sup>2</sup> ) | Energy<br>(MeV) | Range<br>(μm) | V <sub>DS</sub> (V)  |                      |                       |                       |                       |
|-----|----------------------------------|-----------------|---------------|----------------------|----------------------|-----------------------|-----------------------|-----------------------|
|     |                                  |                 |               | @V <sub>GS</sub> =0V | @V <sub>GS</sub> =5V | @V <sub>GS</sub> =10V | @V <sub>GS</sub> =15V | @V <sub>GS</sub> =20V |
| Cu  | 28.0                             | 285             | 43.0          | -200                 | -200                 | -200                  | -200                  | —                     |
| Br  | 36.8                             | 305             | 39.0          | -200                 | -200                 | -125                  | -75                   | —                     |



**Fig a. Typical Single Event Effect, Safe Operating Area**

For footnotes, refer to the last page

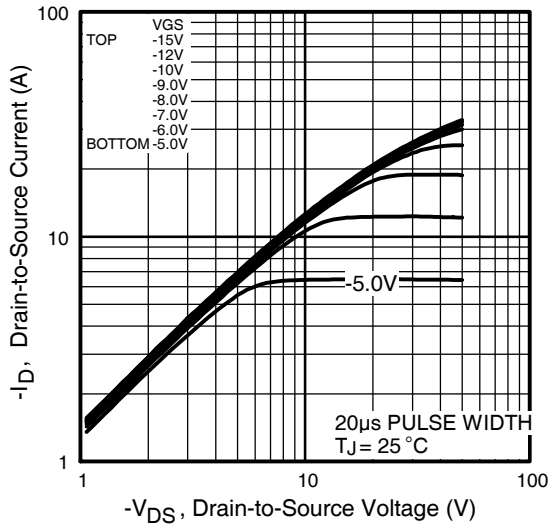


Fig 1. Typical Output Characteristics

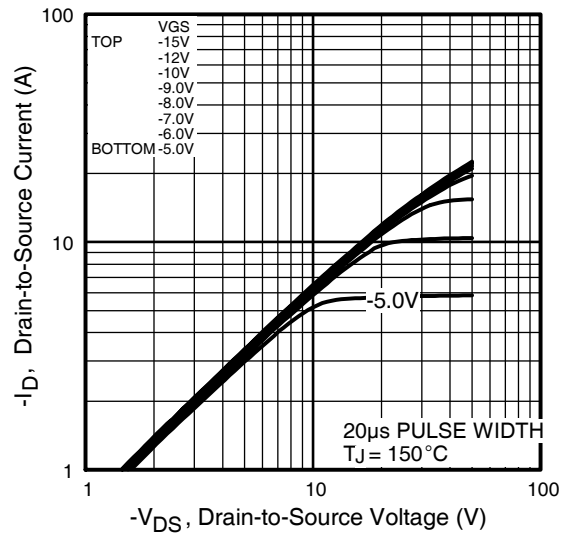


Fig 2. Typical Output Characteristics

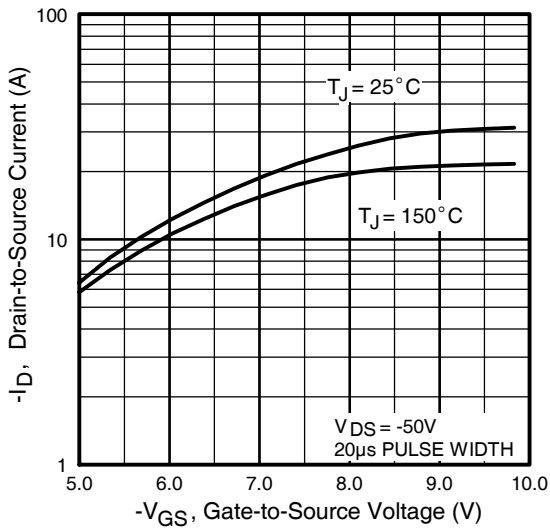


Fig 3. Typical Transfer Characteristics

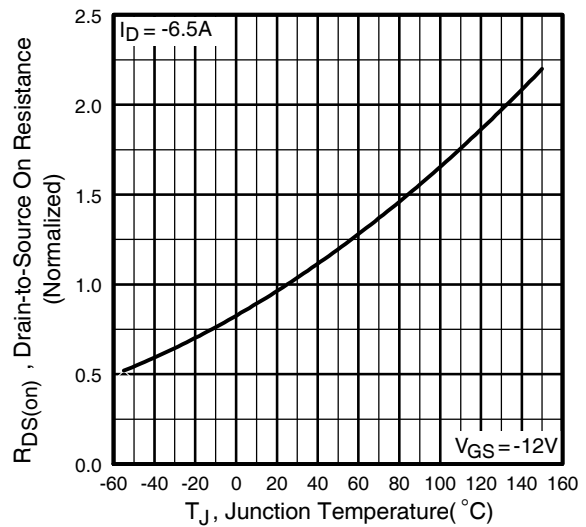


Fig 4. Normalized On-Resistance Vs. Temperature

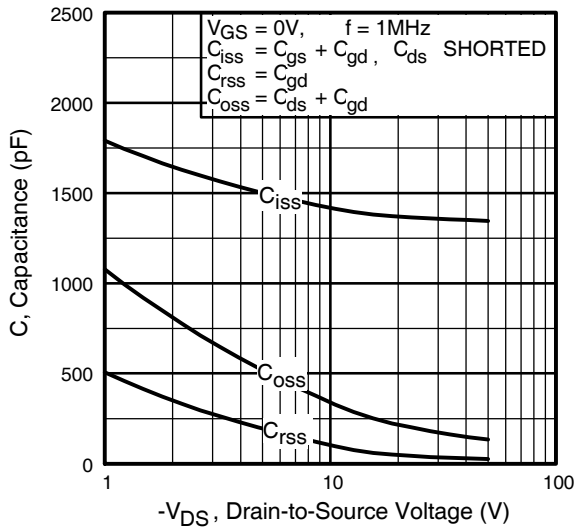


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

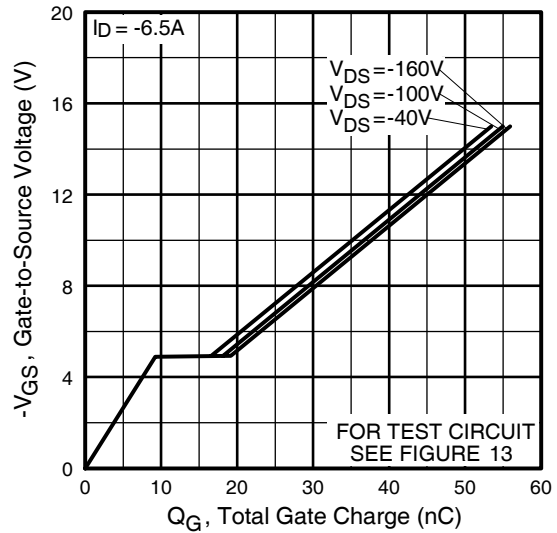


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

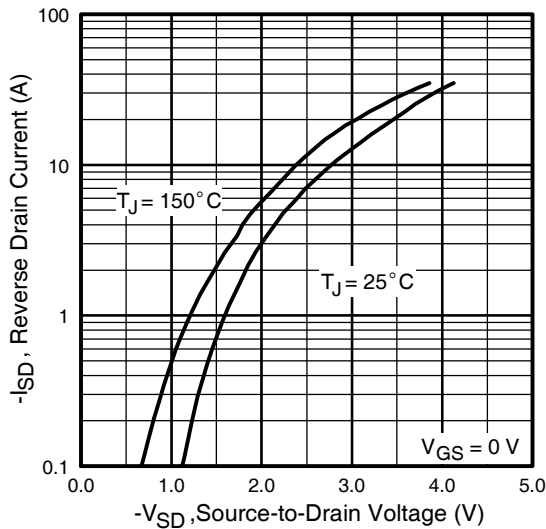


Fig 7. Typical Source-Drain Diode Forward Voltage

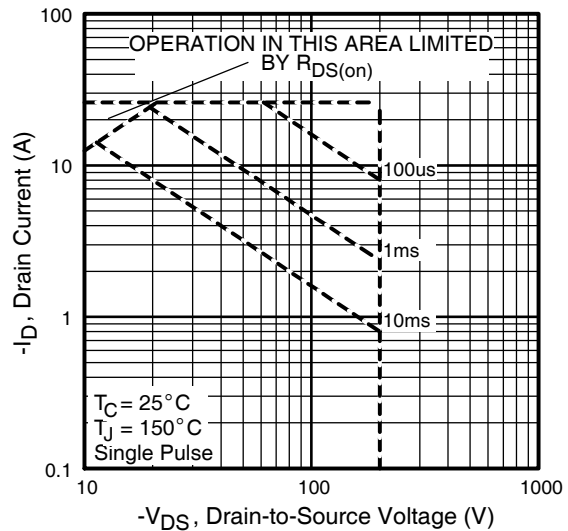


Fig 8. Maximum Safe Operating Area

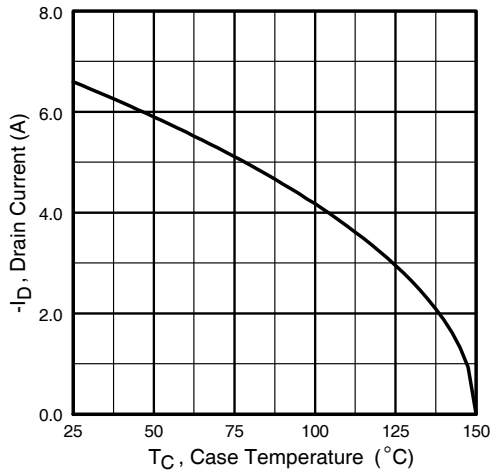


Fig 9. Maximum Drain Current Vs. Case Temperature

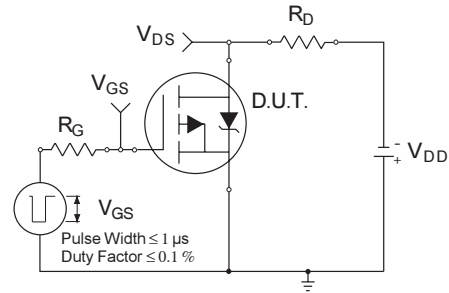


Fig 10a. Switching Time Test Circuit

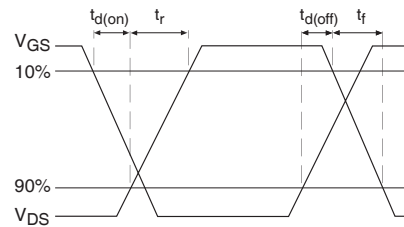


Fig 10b. Switching Time Waveforms

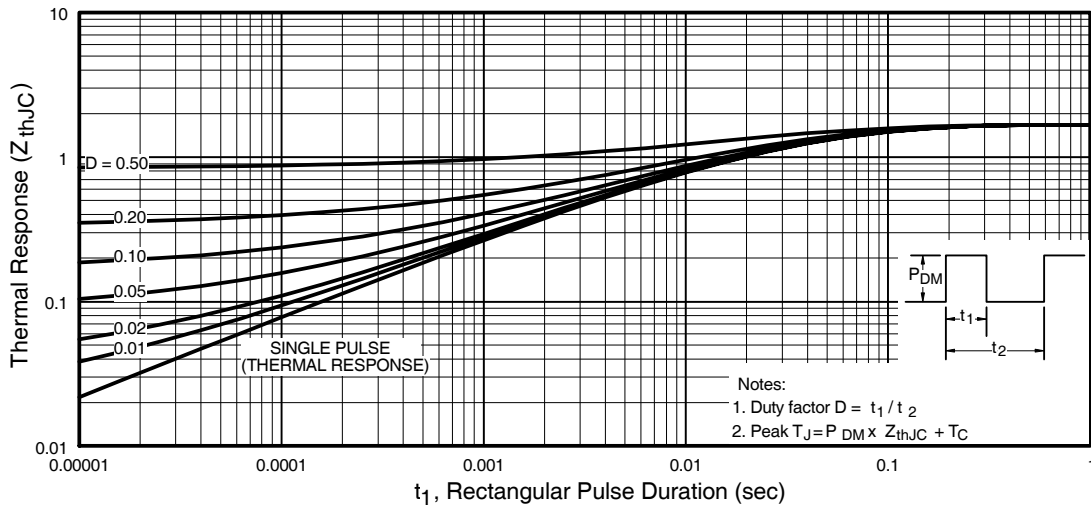


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

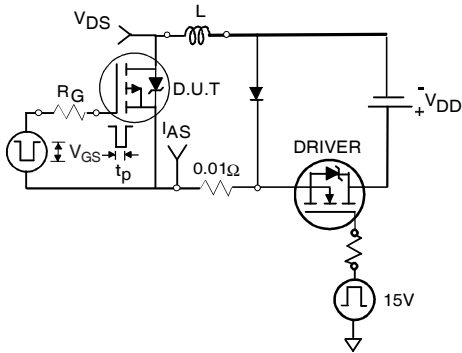


Fig 12a. Unclamped Inductive Test Circuit

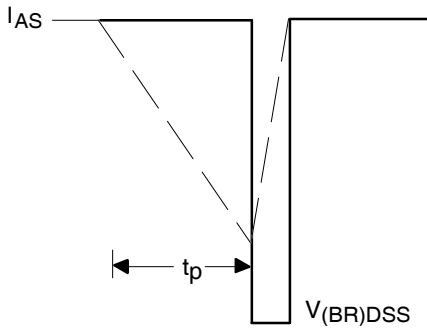


Fig 12b. Unclamped Inductive Waveforms

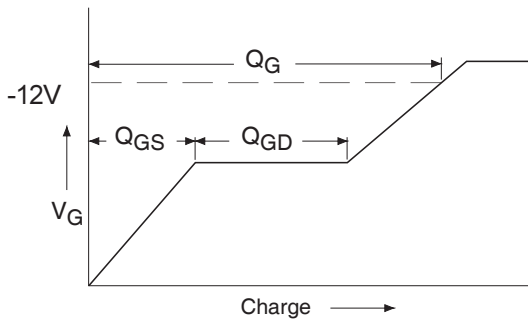


Fig 13a. Basic Gate Charge Waveform

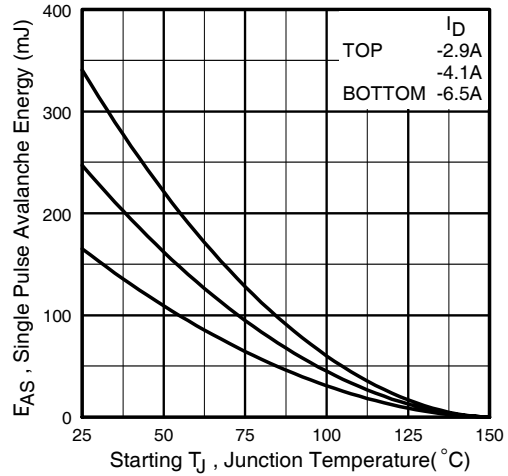


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

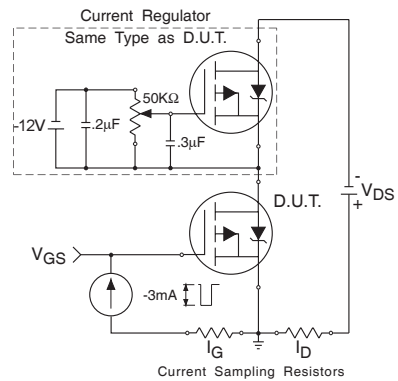
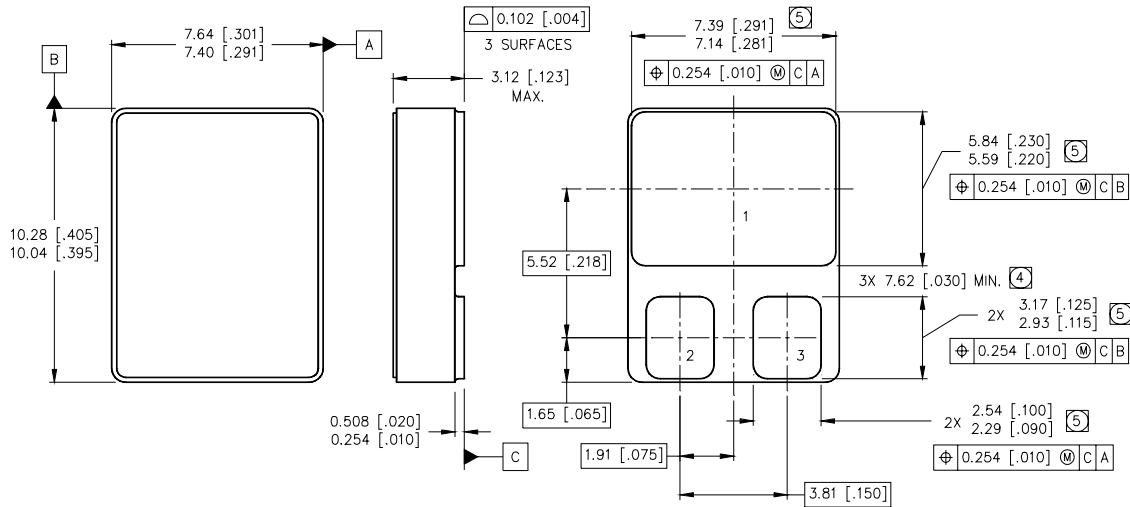


Fig 13b. Gate Charge Test Circuit

**Footnotes:**

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ②  $V_{DD} = -50V$ , starting  $T_J = 25^\circ C$ ,  $L = 11mH$   
Peak  $I_L = -6.5A$ ,  $V_{GS} = -12V$
- ③  $I_{SD} \leq -6.5A$ ,  $di/dt \leq -375A/\mu s$ ,  
 $V_{DD} \leq -200V$ ,  $T_J \leq 150^\circ C$
- ④ Pulse width  $\leq 300 \mu s$ ; Duty Cycle  $\leq 2\%$
- ⑤ **Total Dose Irradiation with  $V_{GS}$  Bias.**  
-12 volt  $V_{GS}$  applied and  $V_{DS} = 0$  during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with  $V_{DS}$  Bias.**  
-160 volt  $V_{DS}$  applied and  $V_{GS} = 0$  during irradiation per MIL-STD-750, method 1019, condition A.

**Case Outline and Dimensions — SMD-0.5**



NOTES:

- 1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- 2. CONTROLLING DIMENSION: INCH.
- 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- ④ DIMENSION INCLUDES METALLIZATION FLASH.
- ⑤ DIMENSION DOES NOT INCLUDE METALLIZATION FLASH.

PAD ASSIGNMENTS

- 1 = DRAIN
- 2 = GATE
- 3 = SOURCE



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